

SKW Associates, Inc.

3370 Victor Court

Santa Clara, CA 95054

Phone: (408) 919-0094

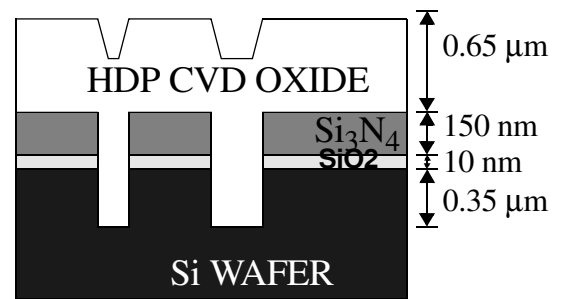
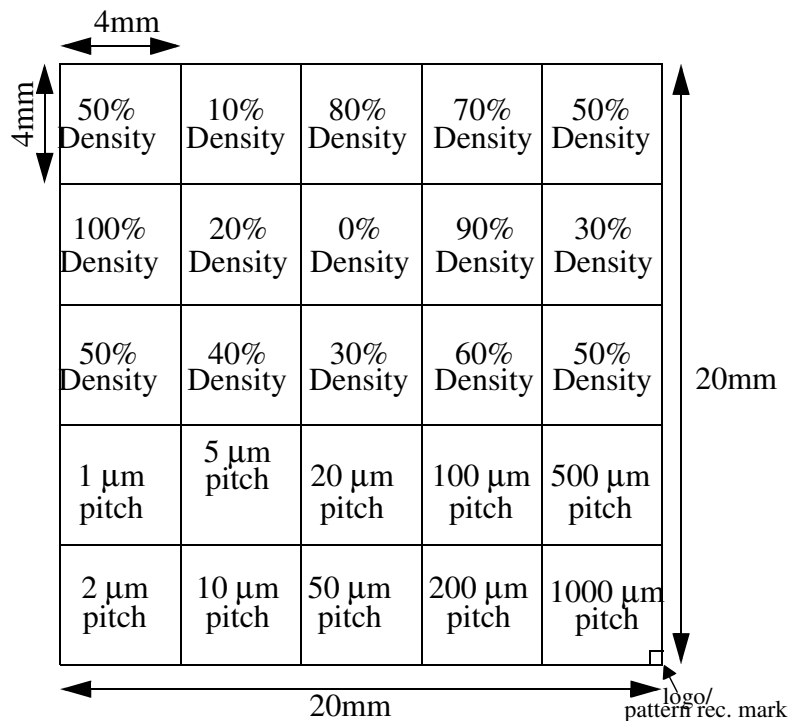
Fax: (408) 919-0097

Email: skw@testwafer.com

<http://www.testwafer.com>

SKW3-764ETC303 300mm Wafer Specifications

DATE: December 09, 2005



Cross Sectional View

SKW3-764ETC303 Mask Floor Plan

| PARAMETER | NOMINAL | TOLERANCE |
|-----------------------|-------------------|-----------------------|
| Patterning | | |
| Center Die X Location | -10.000 mm | +/- 100 μm |
| Center Die Y Location | -10.000 mm | +/- 100 μm |
| Die Size: X | 20 mm | +/- 10 μm |
| Die Size: Y | 20 mm | +/- 10 μm |
| Vertical Die Spacing | 180 μm | +/- 10 % |

| | | |
|--|-------------------------------------|---------------------|
| Horizaontal Spacing | 360 μm | +/- 10 % |
| <i>Linewidth Variation</i> (measured on 10 μm and 90 μm structures) | | |
| Lot-to-Lot | 10 μm , 90 μm | +/- 1 μm |
| Within-Lot (Wafer-to-Wafer) | | +/- 1 μm |
| Within-Wafer | | +/- 1 μm |
| Within-Die | | +/- 1 μm |
| <i>Raisde Area Thickness (HDP CVD Oxide Fill)</i> | | |
| Lot-to-Lot | 0.65 μm | +/- 10 % |
| Within-Lot (Wafer-to-Wafer) | | +/- 10 % |
| Within-Wafer | | +/- 5 % |
| Within-Die | | +/- 5 % |
| <i>Raised Area Thickness (Nitride)</i> | | |
| Lot-to-Lot | 1500 \AA | +/- 10 % |
| Within-Lot (Wafer-to-Wafer) | | +/- 10 % |
| Within-Wafer | | +/- 5 % |
| Within-Die | | +/- 5 % |
| <i>Raised Area Thickness (Pad Oxide)</i> | | |
| Lot-to-Lot | 100 \AA | +/- 10 % |
| Within-Lot (Wafer-to-Wafer) | | +/- 10 % |
| Within-Wafer | | +/- 5 % |
| Within-Die | | +/- 5 % |
| <i>Silicon Trench Depth</i> | | |
| Lot-to-Lot | 3500 \AA | +/- 10 % |
| Within-Lot (Wafer-to-Wafer) | | +/- 10 % |
| Within-Wafer | | +/- 10 % |
| Within-Die | | +/- 10 % |